

9

concentration of from approximately 10^{13} to approximately 10^{14} electrons per cm^3 is present in said base.

6. The DRAM cell of claim 1 whereby during forming of said bipolar transistor, the implanting of the emitter is accomplished by implanting Boron Fluoride (BF_2) at a range of energy of approximately 10 Kev to a concentration of from approximately 10^{15} to approximately 10^{16} holes per cm^3 is present in said emitter.

10

7. The DRAM cell of claim 1 whereby said storage capacitor is from the group of storage capacitors consisting of stacked capacitors, trench capacitors, and capacitances formed between the gate and the source and drain of a second MOS transistors with formed within said DRAM cell.

* * * * *